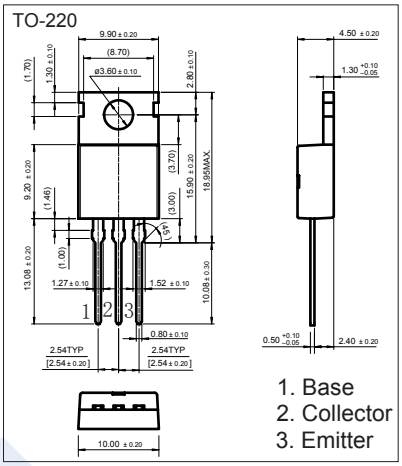
PNP Transistors

KTA1036



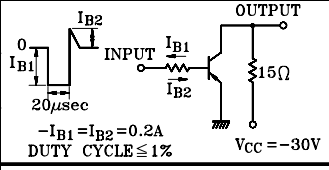
■ Features

- Low Collector Saturation Voltage
- Comlementary to KTC2016

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-60	V
Collector - Emitter Voltage	V_{CEO}	-60	
Emitter - Base Voltage	V_{EBO}	-7	
Collector Current - Continuous	I_C	-3	A
Base Current	I_B	-0.5	
Collector Power Dissipation Ta = 25℃	P_C	2	W
Collector Power Dissipation Tc = 25℃		30	
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 uA, I_E=0	-60			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -50 mA, I_B=0	-60			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 uA, I_C=0	-7			
Collector-base cut-off current	I_{CBO}	V_{CB}= -60V , I_E=0			-0.1	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -7V , I_C=0			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-2 A, I_B=-200mA			-1	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-2 A, I_B=-200mA			-1.2	
Base - emitter voltage	V_{BE}	V_{CE}= -5V, I_C= -500mA			-1	
DC current gain	$h_{FE(1)}$	V_{CE}= -5V, I_C= -500mA	100		300	
	$h_{FE(2)}$	V_{CE}= -5V, I_C= -3 A	20			
Turn On Time	t_{on}			0.4		us
Storage Time	t_{stg}			1.7		
Fall Time	t_f			0.5		
Collector output capacitance	C_{ob}	V_{CB}= -10V, I_E= 0,f=1MHz		45		pF
Transition frequency	f_T	V_{CE}= -5V, I_C= -500mA		30		MHz

■ Classification of $h_{fe(1)}$

Type	KTA1036-Y	KTA1036-G
Range	100-200	150-300

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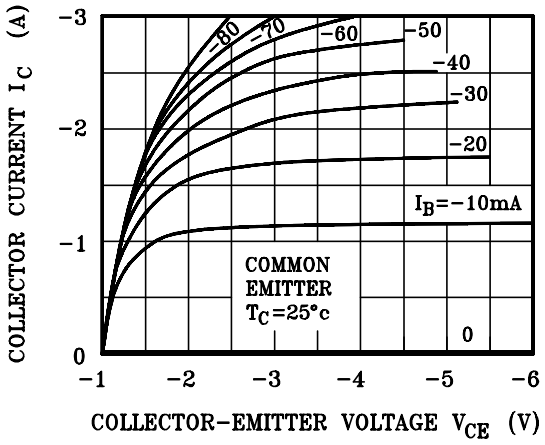
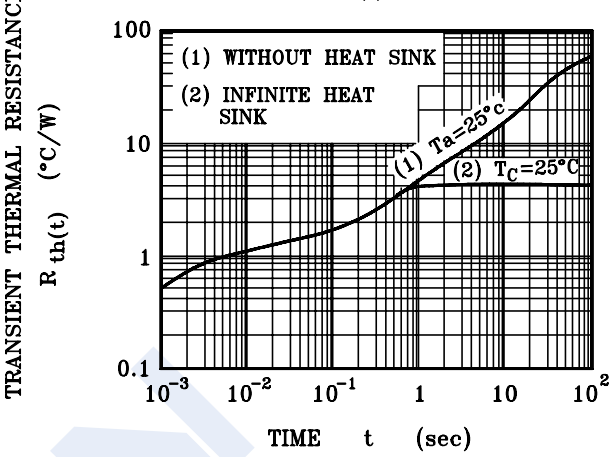
■ Typical Characterisitics

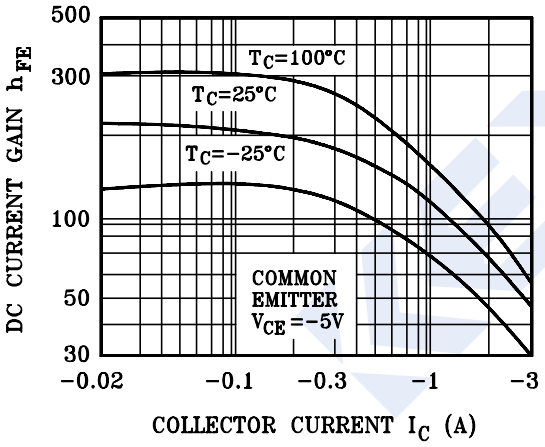
I_C – V_{CE}



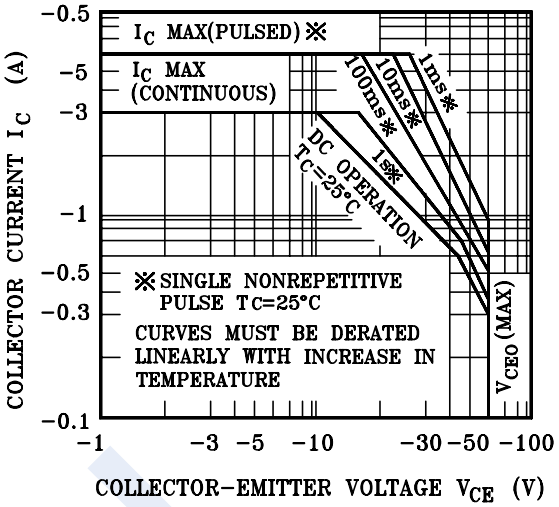
$R_{th(t)}$ – t



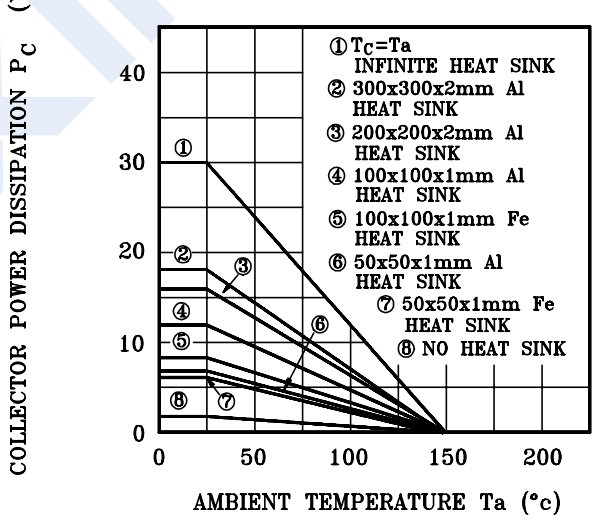
h_{FE} – I_C



SAFE OPERATING AREA



P_C – Ta



$V_{CE(sat)}$ – I_C